Product data sheet

1. General description

Dual common cathode power Schottky diode designed for high frequency switched mode power supplies in a TO220 plastic package.



2. Features and benefits

- Trench structure
- High junction temperature up to 150°C
- Low forward conduction voltage
- Negligible switching losses
- High efficiency

3. Applications

- · DC to DC converters
- · Freewheeling diode
- · OR-ing diode

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Values				
Absolute	maximum rating					
V_{RRM}	repetitive peak reverse voltage		1	00		V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 128 °C; per diode; Fig. 1; Fig. 2; Fig. 3	20			
$I_{O(AV)}$	average output current	δ = 0.5 ; square-wave pulse; $T_{mb} \le$ 126 °C; both diodes conducting	40			А
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
V _F	forward voltage	$I_F = 5 \text{ A}; T_j = 25 \text{ °C}; \text{ per diode}; \underline{\text{Fig. 6}}$	-	0.48	-	V
		I _F = 5 A; T _j = 125 °C; per diode; <u>Fig. 6</u>	-	0.41	-	V
		$I_F = 20 \text{ A}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 6$	-	0.71	0.78	V
		I _F = 20 A; T _j = 125 °C; per diode; <u>Fig. 6</u>	-	0.64	0.71	V
I _R	reverse current	$V_R = 100 \text{ V}; T_j = 25 \text{ °C}; \text{ per diode}; $ Fig. 7; Fig. 8	-	-	50	μΑ
		$V_R = 100 \text{ V}; T_j = 125 \text{ °C}; \text{ per diode}; $ Fig. 7; Fig. 8	-	-	30	mA

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WNS40100C

Dual power Schottky diode

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	К	cathode		A1
3	A2	anode 2		K sym125
mb	К	mounting base; connected to cathode		Symrzo

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WNS40100C	TO220	WNS40100CQ	Tube	50	TO220E	26-April-2019

7. Marking

Table 4. Marking codes

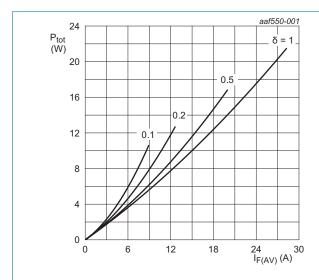
Type number	Marking codes
WNS40100C	WNS 40100C

8. Limiting values

Table 5. Limiting values

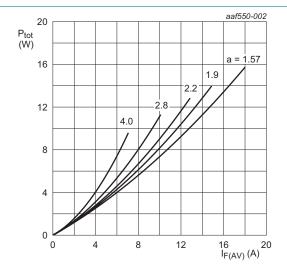
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		100	V
V_{RWM}	crest working reverse voltage		100	V
V_R	reverse voltage	DC	100	V
$I_{F(AV)}$	average forward current	$δ$ = 0.5 ; square-wave pulse; $T_{mb} \le 128$ °C; per diode; Fig. 1; Fig. 2; Fig. 3	20	А
$I_{O(AV)}$	average output current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le$ 126 °C; both diodes conducting	40	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	330	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	363	А
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C



 $\begin{aligned} I_{\text{F(AV)}} &= I_{\text{F(RMS)}} \times \sqrt{\delta} \\ V_{\text{o}} &= 0.562 \text{ V; } R_{\text{s}} = 0.0070 \text{ } \Omega \end{aligned}$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode



a = form factor = $I_{F(RMS)}$ / $I_{F(AV)}$ V_o = 0.562 V; R_s = 0.0070 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

Dual power Schottky diode

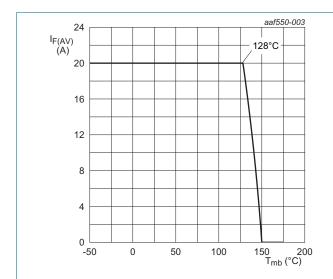


Fig. 3. Average forward current as a function of mounting base temperature; maximum values; per diode

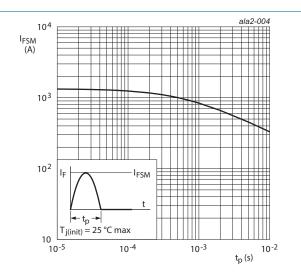


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

Dual power Schottky diode

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to	per diode; Fig. 5	-	-	1.3	K/W
	mounting base	both diodes conducting	-	-	0.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

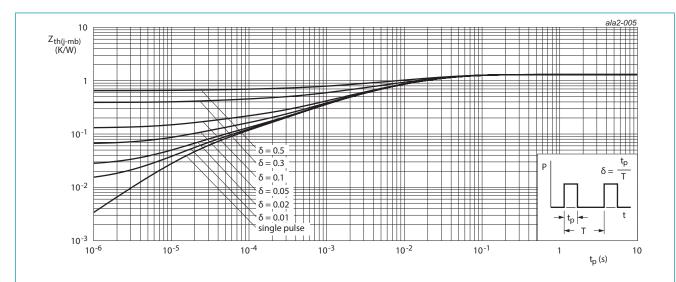


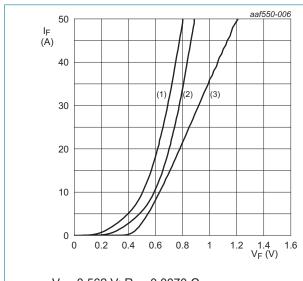
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values; per diode

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
V _F forwa	forward voltage	I _F = 5 A; T _j = 25 °C; per diode; <u>Fig. 6</u>	-	0.48	-	V
		I _F = 5 A; T _j = 125 °C; per diode; <u>Fig. 6</u>	-	0.41	-	V
		I _F = 20 A; T _j = 25 °C; per diode; <u>Fig. 6</u>	-	0.71	0.78	V
		I _F = 20 A; T _j = 125 °C; per diode; <u>Fig. 6</u>	-	0.64	0.71	V
I _R reverse current		$V_R = 100 \text{ V}; T_j = 25 \text{ °C}; \text{ per diode}; $ Fig. 7; Fig. 8	-	-	50	μA
		$V_R = 100 \text{ V}; T_j = 125 ^{\circ}\text{C}; \text{ per diode}; $ Fig. 7; Fig. 8	-	-	30	mA



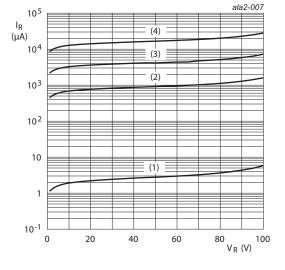
 $V_o = 0.562 \text{ V}; R_s = 0.0070 \Omega$

(1) $T_j = 150 \, ^{\circ}\text{C}$; typical values

(2) T_j = 150 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage; per diode



(1) T_i = 25 °C; typical values

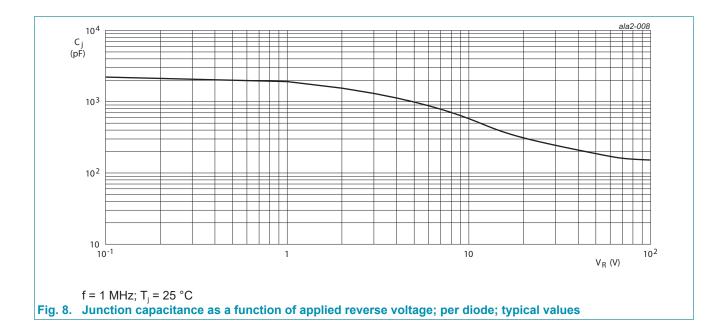
(2) T_j = 100 °C; typical values

(3) $T_j = 125$ °C; typical values

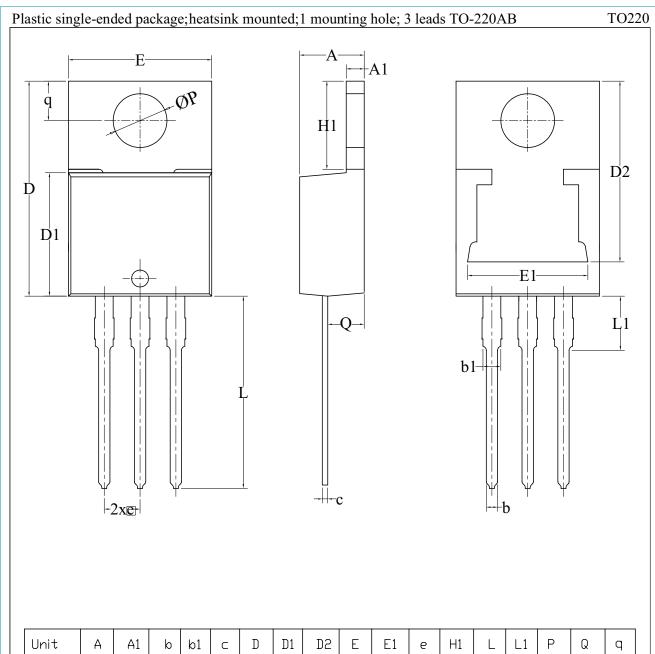
(4) T_i = 150 °C; typical values

Fig. 7. Reverse leakage current as a function of reverse voltage; per diode; typical values

Dual power Schottky diode



11. Package outline



Ur	nit	Α	A1	b	b1	С	D	D1	D2	Ε	E1	е	H1	L	L1	Р	Q	Р
MM	min	4.35	1.14	0.69	1.20	0.36	14.95	8,50	12.20	10.00	8.25	254	6.00	13.00	3.40	3.70	2.40	2.60
MM	max	4.75	1.40	1.01	1.45	0.61	15.55	9.02	12.88	10.40	8.89	(BSC)	6.40	14.00	3.80	3,95	2,80	3.00

Dual power Schottky diode

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Dual power Schottky diode

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Dual power Schottky diode

13. Contents

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	3
9. Thermal characteristics	5
10. Characteristics	6
11. Package outline	8
12. Legal information	9
13. Contents	

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